

Cancel
providing a semiconductor structure having [the] a base layer,
[the] an insulation layer, and [the] a monocrystalline silicon
layer;

introducing [the] a passivating substance X [into one of]
between the insulation layer and the monocrystalline silicon
layer [during or after the fabrication of the semiconductor
structure]; and

B
heat-treating the semiconductor structure with the passivating
substance X, thereby, causing the passivating substance to
diffuse into an interface between the insulation layer and the
monocrystalline silicon layer.

Cancel
Claim 12 (amended). The method according to claim 7, which
comprises patterning the monocrystalline silicon layer by
etching away regions thereof down to [the] an underlying
insulation layer.

Remarks:

Reconsideration of the application is requested.

Claims 1-15 are remain in the application. Claims 7 and 12
have been amended. Claims 1-6 have been withdrawn from
consideration.